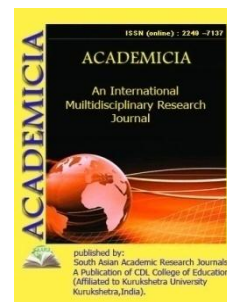




**ACADEMICIA**  
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 (Double Blind Refereed & Peer Reviewed Journal)



**DOI: 10.5958/2249-7137.2021.01439.7**

## IRON ADMINISTRATION IN GALLIUM ARSENIDE

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### ABSTRACT

*Based on the data obtained by nuclear gamma-resonance spectroscopy, it is concluded that the state of impurity atoms depends both on the type of conductivity and on whether these atoms are in the surface layer or in the bulk of semiconductors.*

**KEYWORDS:** *Iron, Nuclear Gamma-Resonance Spectroscopy, Impurity Atoms, Surface Layer, Bulk of Semiconductors.*

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### REFERENCES:

1. Turaev E.Yu., Seregin PP, "The nature of the state formed by tin and iron atoms in arsenic selenide" UFZh, 1991, pp. 81-85.
2. Turaev E.Yu. et al. "The nature of the electrical inactivity of impurity atoms in the gallium-tellurium system." Physics and chemistry of glass, 1987, v. 13, pp. 696-700.
3. Turaev E.Yu. et al. "Study of the state of impurity atoms in amorphous silicon." Inorganic materials, 1991, vol. 27, p. 899-903.
4. Turaev E.Yu. et al. Seregin PP, "Investigation by the Mössbauer method of the effect of the crystal-glass transition on the structure of semiconductors." Letter to ZhETF, no. 2, 1974, pp. 81-82.
5. Turaev E.Yu., Seregin PP, "Electronic spectra of crystalline and glassy arsenic chalcogenides." Physics and chemistry of glass, 1977, vol. 3, no. 5 pp. 103-106.